

<i>Notice of References Cited</i>	Application/Control No. 10/531,391	Applicant(s)/Patent Under Reexamination WATANABE ET AL.	
	Examiner XNNING NIU	Art Unit 2828	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0039374	04-2002	Onomura et al.	372/46
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	T. Chino et al., "High Reliable InGaAsP Buried Heterostructure Laser Diode Fabricated by Cl <sub>2</sub> /N <sub>2</sub> -RIBE and MOVPE," 10 <sup>th</sup> Intern. Conf. on Indium Phosphide and Related materials, pps 709-712, 1998.
	V	Tojoyo et al., "High-Power AlGaInN Laser Diodes with High Kink level and Low Relative Intensity Noise," Jpn. J. Appl. Phys, Vol. 41, pps 1829-1833, 2002.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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